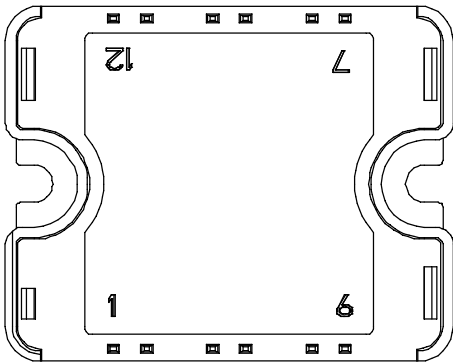
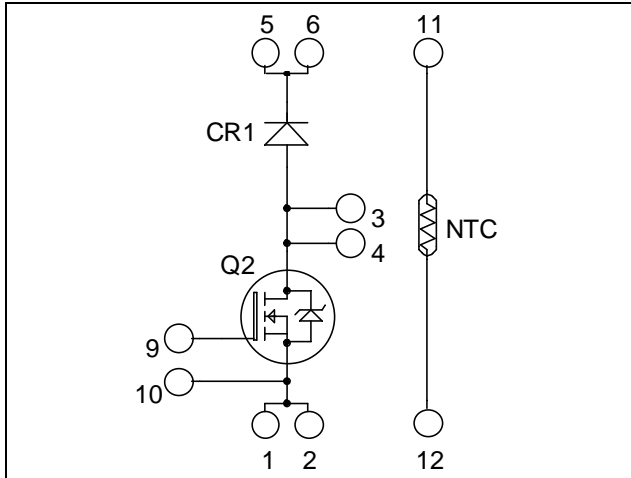


Boost chopper MOSFET Power Module

$V_{DSS} = 1000V$
 $R_{DSon} = 180m\Omega$ typ @ $T_j = 25^\circ C$
 $I_D = 40A$ @ $T_c = 25^\circ C$



Pins 1/2 ; 3/4 ; 5/6 must be shorted together

Application

- AC and DC motor control
- Switched Mode Power Supplies
- Power Factor Correction

Features


- Power MOS 8TM MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Very low stray inductance
- Internal thermistor for temperature monitoring
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	1000	V
I_D	Continuous Drain Current	$T_c = 25^\circ C$	40
		$T_c = 80^\circ C$	30
I_{DM}	Pulsed Drain current	260	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	216	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^\circ C$	657
I_{AR}	Avalanche current (repetitive and non repetitive)	33	A


CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 1000\text{V}$ $V_{GS} = 0\text{V}$	$T_j = 25^\circ\text{C}$			100	μA
			$T_j = 125^\circ\text{C}$			500	
$R_{DS(on)}$	Drain – Source on Resistance	$V_{GS} = 10\text{V}, I_D = 33\text{A}$		180	216	$\text{m}\Omega$	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 2.5\text{mA}$	3	4	5	V	
I_{GSS}	Gate – Source Leakage Current	$V_{GS} = \pm 30\text{V}$			± 100	nA	

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}$ $V_{DS} = 25\text{V}$ $f = 1\text{MHz}$		14800		pF
C_{oss}	Output Capacitance			1555		
C_{rss}	Reverse Transfer Capacitance			196		
Q_g	Total gate Charge	$V_{GS} = 10\text{V}$ $V_{Bus} = 500\text{V}$ $I_D = 33\text{A}$		570		nC
Q_{gs}	Gate – Source Charge			100		
Q_{gd}	Gate – Drain Charge			270		
$T_{d(on)}$	Turn-on Delay Time	Resistive switching @ 25°C $V_{GS} = 15\text{V}$ $V_{Bus} = 667\text{V}$ $I_D = 33\text{A}$ $R_G = 2.2\Omega$		85		ns
T_r	Rise Time			75		
$T_{d(off)}$	Turn-off Delay Time			285		
T_f	Fall Time			70		

Chopper diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
V_{RRM}	Maximum Peak Repetitive Reverse Voltage		1200			V	
I_{RM}	Maximum Reverse Leakage Current	$V_R = 1200\text{V}$	$T_j = 25^\circ\text{C}$			100	μA
			$T_j = 125^\circ\text{C}$			500	
I_F	DC Forward Current	$T_c = 80^\circ\text{C}$		60		A	
V_F	Diode Forward Voltage	$I_F = 60\text{A}$		2.5	3	V	
		$I_F = 120\text{A}$		3			
		$I_F = 60\text{A}$	$T_j = 125^\circ\text{C}$	1.8			
t_{rr}	Reverse Recovery Time	$I_F = 60\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		265	ns	
			$T_j = 125^\circ\text{C}$		350		
Q_{rr}	Reverse Recovery Charge	$I_F = 60\text{A}$ $V_R = 800\text{V}$ $di/dt = 200\text{A}/\mu\text{s}$	$T_j = 25^\circ\text{C}$		560	nC	
			$T_j = 125^\circ\text{C}$		2890		

Thermal and package characteristics

Symbol	Characteristic	Min	Typ	Max	Unit	
R_{thJC}	Junction to Case Thermal Resistance	Transistor			0.19	$^\circ\text{C}/\text{W}$
		Diode			0.9	
V_{ISOL}	RMS Isolation Voltage, any terminal to case $t = 1\text{min}$, $I_{isol} < 1\text{mA}$, 50/60Hz	2500			V	
T_j	Operating junction temperature range	-40		150	$^\circ\text{C}$	
T_{STG}	Storage Temperature Range	-40		125		
T_C	Operating Case Temperature	-40		100		
Torque	Mounting torque	To heatsink	M4	2.5	4.7	N.m
Wt	Package Weight				80	g

Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

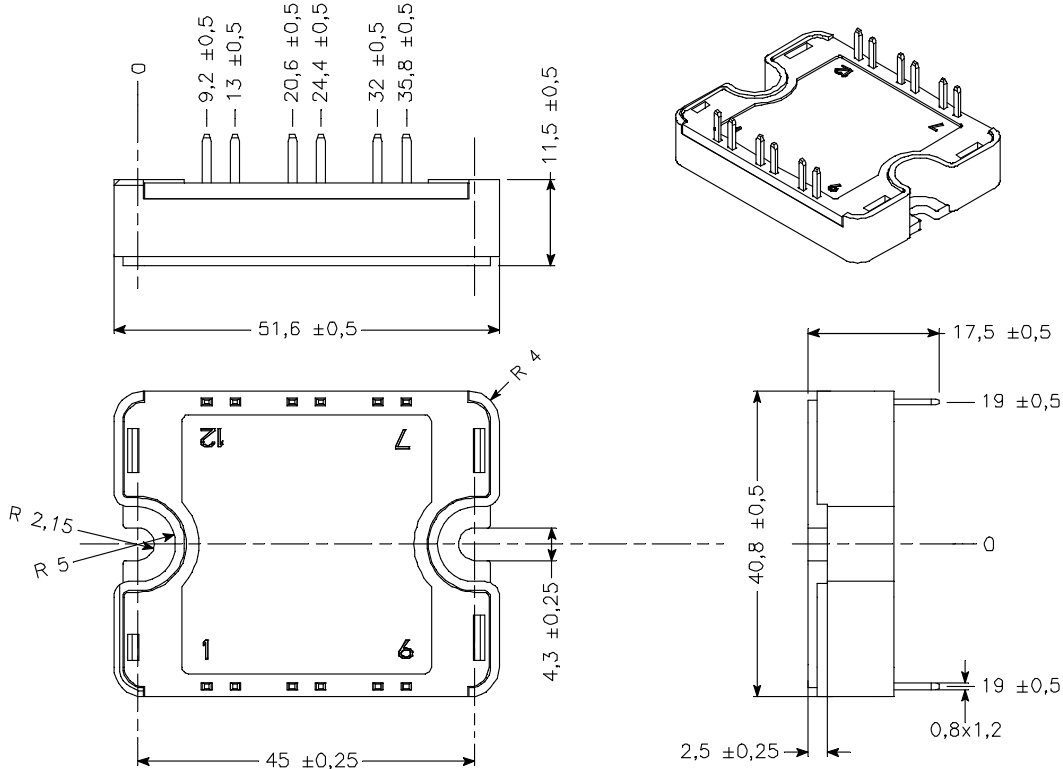
Symbol Characteristic

		<i>Min</i>	<i>Typ</i>	<i>Max</i>	<i>Unit</i>
R ₂₅	Resistance @ 25°C		50		kΩ
B _{25/85}	T ₂₅ = 298.15 K		3952		K

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$

T: Thermistor temperature
 R_T: Thermistor value at T

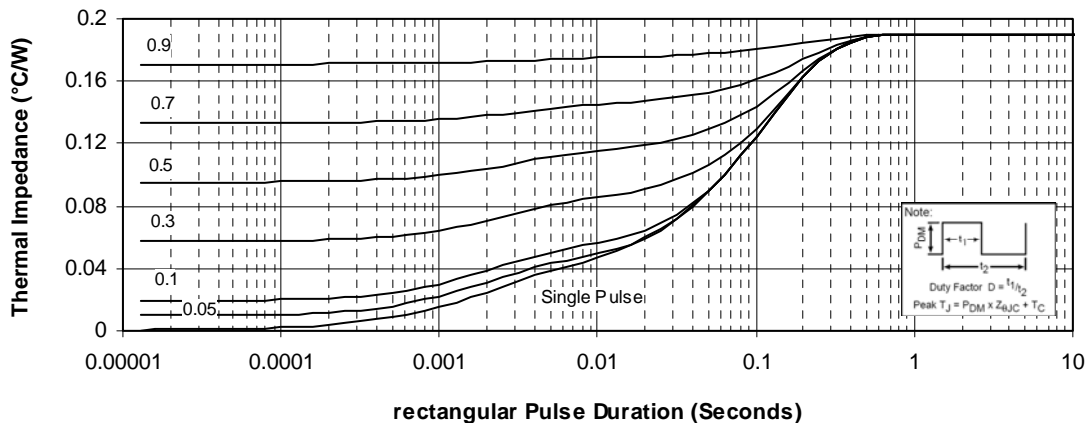
SP1 Package outline (dimensions in mm)

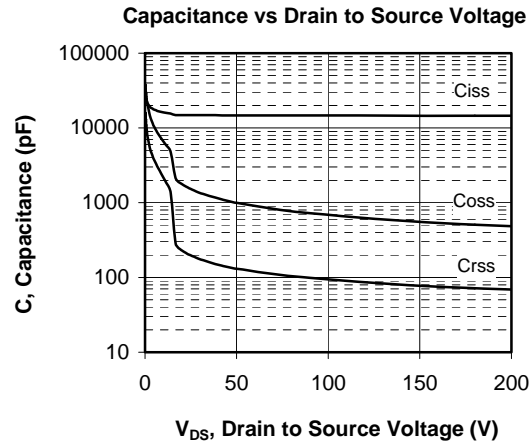
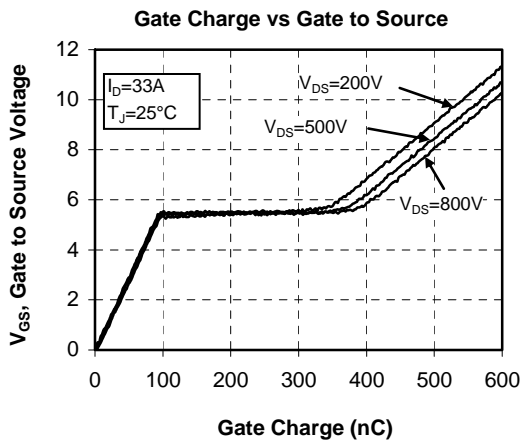
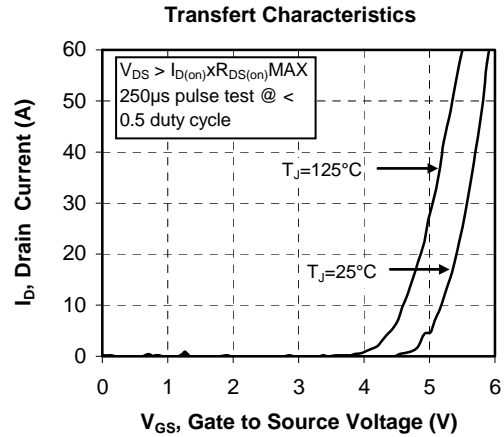
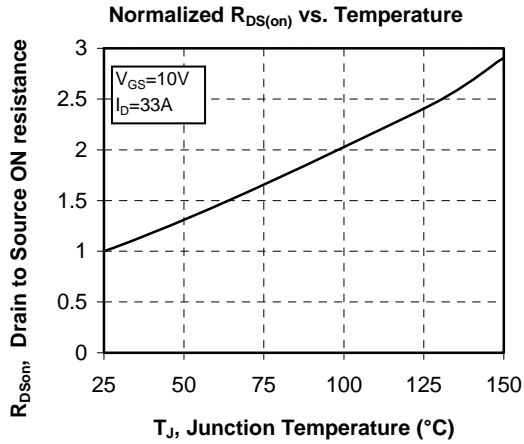
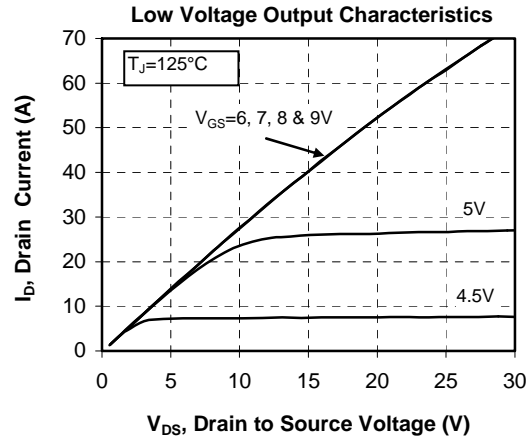
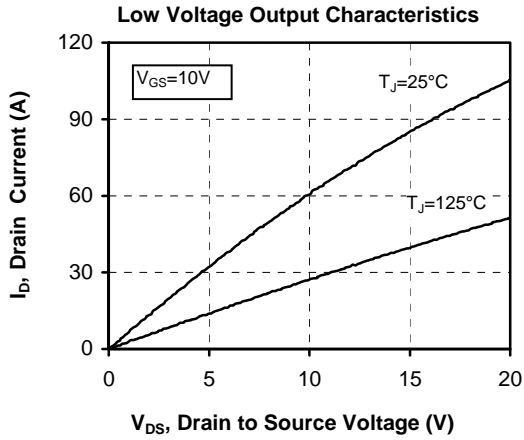


See application note 1904 - Mounting Instructions for SP1 Power Modules on www.microsemi.com

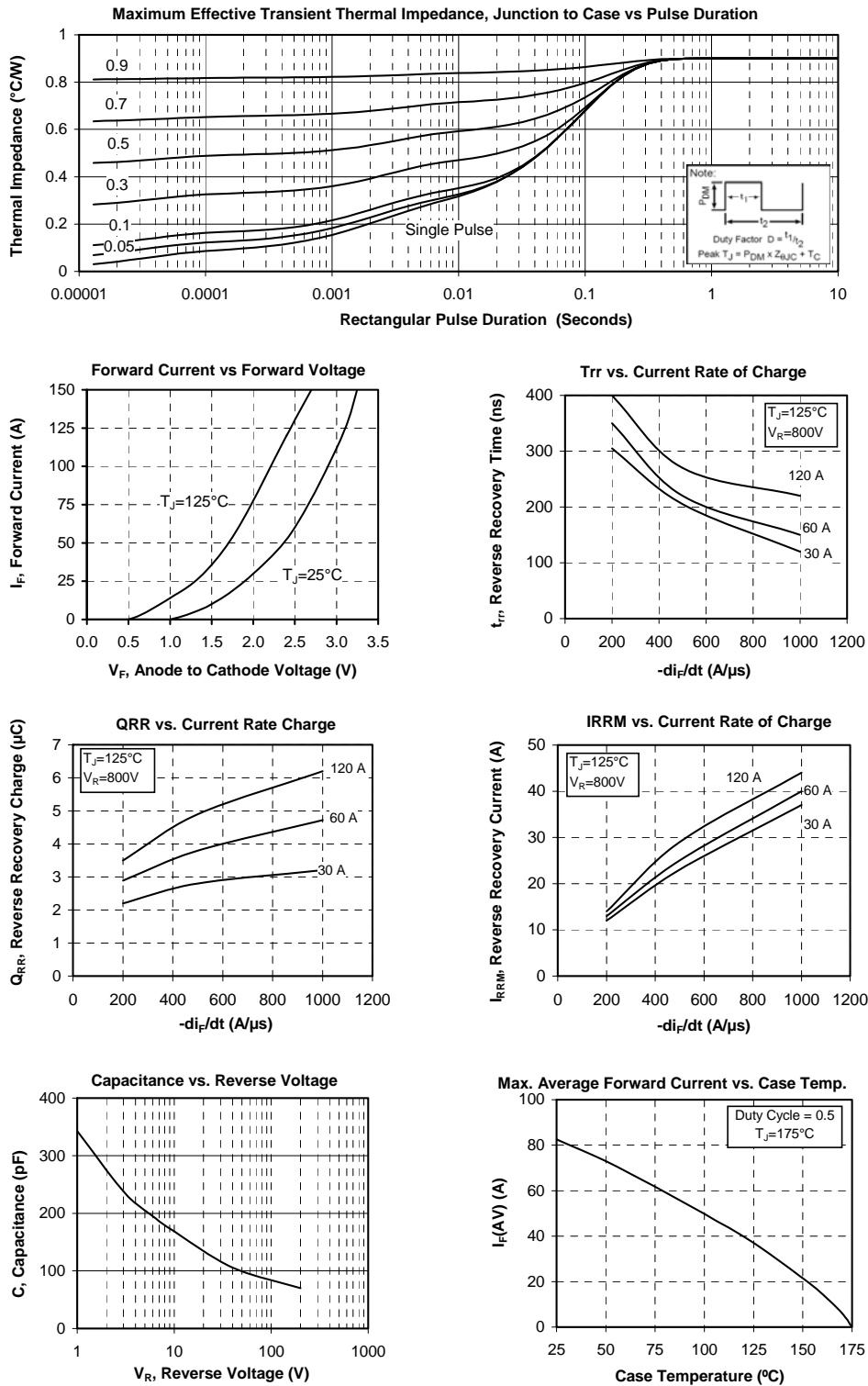
Typical Mosfet Performance Curve

Maximum Effective Transient Thermal Impedance, Junction to Case vs Pulse Duration





Typical Diode Performance Curve



Microsemi reserves the right to change, without notice, the specifications and information contained herein

Microsemi's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S and Foreign patents pending. All Rights Reserved.